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a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

at least one contact for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions;

and

a plurality of current divider segments unevenly and randomly distributed within the first diffusion region.

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92. (Amended) An electrostatic discharge protection device, comprising:

a substrate;

a first diffusion region formed in the substrate;

a second diffusion region formed in the substrate adjacent to and spaced from the first diffusion region;

contacts for making a conductive connection to the first diffusion region;

a channel formed in a third region between the first and second diffusion regions;

and

a plurality of current divider segments formed within the first diffusion region and being unevenly and randomly distributed therein.

100. (Amended) The device of claim 99, wherein said segments include the first segment formed of a polysilicon layer or a field oxide layer; and the second segment formed of a polysilicon layer or a field oxide layer.

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